

- Designed for Complementary Use with BD645, BD647, BD649 and BD651
- 62.5 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 3 A

Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
	BD646		-80	
Collector-base voltage (I _E = 0)	BD648	V	-100	V
	BD650	V _{CBO}	-120	
	BD652		-140	
	BD646		-60	
Collector-emitter voltage ($I_B = 0$)	BD648	V	-80	V
	BD650	V _{CEO}	-100	
	BD652		-120	
Emitter-base voltage			-5	V
Continuous collector current			-8	Α
Peak collector current (see Note 1)			-12	Α
Continuous base current			-0.3	Α
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P _{tot}	62.5	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P _{tot}	2	W
Unclamped inductive load energy (see Note 4)		½Ll _C ²	50	mJ
Operating junction temperature range		T _j	-65 to +150	°C
Storage temperature range		T _{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T _L	260	°C

NOTES: 1. This value applies for $t_p \le 0.3$ ms, duty cycle $\le 10\%$.

- 2. Derate linearly to 150° C case temperature at the rate of 0.4 W/° C.
- 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -5 mA, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.



electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER TEST CONDITIONS			MIN	TYP	MAX	UNIT			
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -30 mA	I _B = 0	(see Note 5)	BD646 BD648 BD650 BD652	-60 -80 -100 -120			V
I _{CEO}	Collector-emitter cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -40 \text{ V}$ $V_{CE} = -50 \text{ V}$ $V_{CE} = -60 \text{ V}$	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$		BD646 BD648 BD650 BD652			-0.5 -0.5 -0.5 -0.5	mA
Ісво	Collector cut-off current	V _{CB} = -120 V	$I_{E} = 0$	$T_{C} = 150^{\circ}\text{C}$ $T_{C} = 150^{\circ}\text{C}$ $T_{C} = 150^{\circ}\text{C}$ $T_{C} = 150^{\circ}\text{C}$	BD646 BD648 BD650 BD652 BD646 BD648 BD650 BD652			-0.2 -0.2 -0.2 -0.2 -2.0 -2.0 -2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	I _C = 0	(see Notes 5 and 6)				-5	mA
h _{FE}	Forward current transfer ratio	V _{CE} = -3 V	I _C = -3 A	(see Notes 5 and	i 6)	750			
V _{CE(sat)}	Collector-emitter saturation voltage	$I_B = -12 \text{ mA}$ $I_B = -50 \text{ mA}$	O	(see Notes 5 and	i 6)			-2 -2.5	٧
V _{BE(sat)}	Base-emitter saturation voltage	I _B = -50 mA	I _C = -5 A	(see Notes 5 and	d 6)			-3	٧
V _{BE(on)}	Base-emitter voltage	V _{CE} = -3 V	I _C = -3 A	(see Notes 5 and	i 6)			-2.5	٧

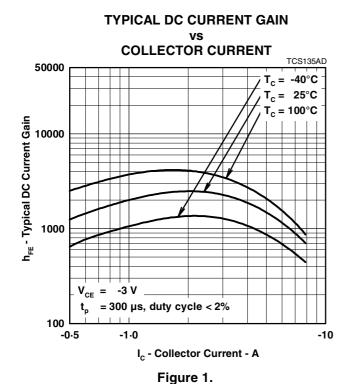
NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu s$, duty cycle $\leq 2\%$.

thermal characteristics

	PARAMETER		TYP	MAX	UNIT
$R_{\theta J}$	Junction to case thermal resistance			2.0	°C/W
$R_{\theta J}$	Junction to free air thermal resistance			62.5	°C/W

^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS



COLLECTOR-EMITTER SATURATION VOLTAGE

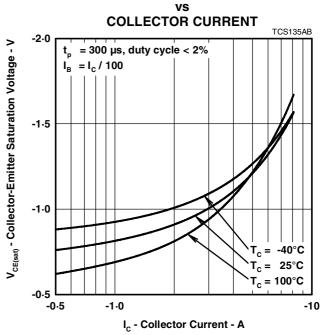
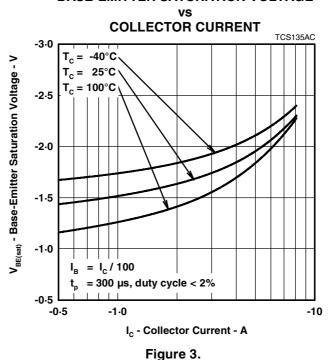


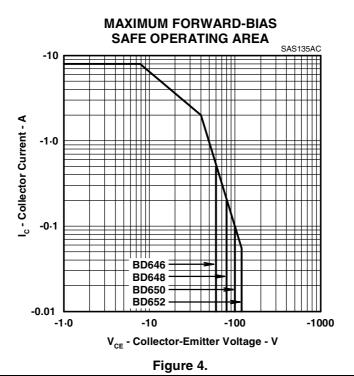
Figure 2.

BASE-EMITTER SATURATION VOLTAGE



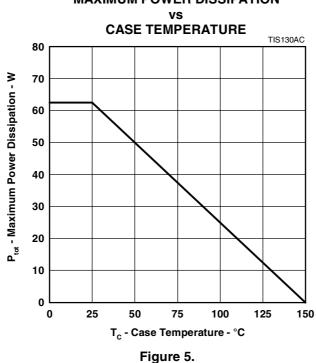
PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

MAXIMUM POWER DISSIPATION



PRODUCT INFORMATION